IN THE CLAIMS

Please amend the claims as follows. This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (currently amended) A~~n~~ product suitable for simulating a standard wafer in semiconductor manufacturing equipment, comprising:

a first layer composed of a material suitable for being handled by the semiconductor manufacturing equipment; and

a second layer composed of a mixture of multiple materials disposed entirely over the first layer, the mixture of the multiple materials configured to simultaneously generate byproducts during an etching operation, wherein the byproducts are selected from the group consisting of aluminum, silicon, tungsten, tungsten silicide, titanium, titanium nitride, silicon dioxide, platinum, ruthenium, ruthenium oxide, copper, tantalum, and nickel ~~similar to byproducts produced by the standard wafer~~.

2. (previously presented) The product of claim 1, wherein the multiple materials include a photoresist and a metal.

3. (previously presented) The product of claim 1, wherein the multiple materials include both a polymer and a material selected from the group consisting of silicon, tungsten, tungsten silicide, titanium, titanium nitride, silicon dioxide, aluminum, platinum, ruthenium, ruthenium oxide, copper, tantalum, and nickel.

Claims 4-15 (canceled)

16. (previously presented) The product of claim 1, wherein the mixture of multiple materials includes three or more materials.

17. (previously presented) The product of claim 1, wherein the second layer is capable of withstanding cumulative etching time of up to 120 radio frequency minutes.

18. (previously presented) The product of claim 1, wherein the mixture of the multiple materials are baked on the first layer.

19. (previously presented) The apparatus of claim 1, wherein a ratio of the multiple materials in the mixture corresponds to an exposed area on the standard wafer being simulated.

Claims 20-39 (canceled)

Claims 40-58 (canceled)